

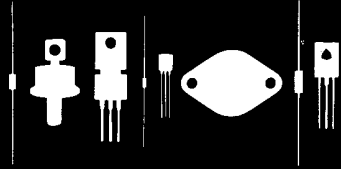
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145 Adams Avenue
Hauppauge, New York 11788



2N3246

NPN SILICON LOW NOISE TRANSISTOR

JEDEC TO-18 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N3246 is an NPN silicon transistor manufactured by the epitaxial planar process designed for small signal, low noise and low power audio amplifier applications.

MAXIMUM RATINGS (TA=25°C)

	SYMBOL		UNIT
Collector-Base Voltage	VCBO	60	V
Collector-Emitter Voltage	VCEO	45	V
Emitter-Base Voltage	VEBO	10	V
Collector Current	IC	50	mA
Power Dissipation	PD	350	mW
Operating and Storage Junction Temperature	TJ, TSTG	-65 TO +200	°C
Thermal Resistance	θJA	0.5	°C/mW

ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
ICBO	VCB=40V		1.0	nA
ICBO	VCB=40V, TA=150°C		2.0	µA
IEBO	VEB=8.0V		1.0	nA
BVCBO	IC=10µA	60		V
BVCEO	IC=1.0mA	45		V
BVEBO	IE=10µA	10		V
VCE(SAT)	IC=5.0mA, IB=0.5mA		0.5	V
VBE(SAT)	IC=5.0mA, IB=0.5mA	0.7	0.9	V
hFE	VCE=5.0V, IC=1.0µA	150		
hFE	VCE=5.0V, IC=10µA	200	600	
hFE	VCE=5.0V, IC=100µA	300		
hFE	VCE=5.0V, IC=500µA	350		
hFE	VCE=5.0V, IC=1.0mA	400	-	
hFE	VCE=5.0V, IC=10mA	-	800	
fT	VCE=5.0V, IC=1.0mA, f=30MHz	60	180	MHz
hfe	VCB=6.0V, IC=1.0mA, f=1.0kHz	200	600	
hib	VCB=6.0V, IC=1.0mA, f=1.0kHz	24	32	Ω
hob	VCB=6.0V, IC=1.0mA, f=1.0kHz	0.1	1.0	µmho
hrb	VCB=6.0V, IC=1.0mA, f=1.0kHz		6X10 ⁻⁴	
Cob	VCB=5.0V, IE=0, f=1.0MHz		5.0	pF
NF	VCE=5.0V, IC=10µA, RG=10kΩ, f=5.0Hz to 15kHz		2.0	dB

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